TOSHIBA CCD Linear Image Sensor CCD (Charge Coupled Device)

TCD2707D

The TCD2707D is a high sensitive and low dark current 7450 elements \times 4 line CCD color image sensor.

The sensor is designed for color scanner.

The device contains a row of 7450 elements \times 4 line photodiodes which provide a 24 lines/mm across a A3 size paper. The device is operated by 5-V pulse, and 10-V power supply.

Features

- Number of image sensing pixels: 7450 elements × 4 lines
- Image sensing pixels size: 4.7 μm by 4.7 μm on 4.7 μm center
- Photo sensing region: High sensitive pn photodiode
- Clock: 2-phase (5 V)
- Distance between photodiode array: Pixel R to pixel G, and pixel G to pixel B = 37.6 μ m (8 lines) Pixel B to pixel B/W = 56.4 μ m (12 lines)
- Internal circuit: Clamp circuitPackage: 22-pin CERDIP
- Color filter: Red, green, blue

Pin Connections (top view)

Weight: 5.2 g (typ.)

WDIP22-G-400-2.54D

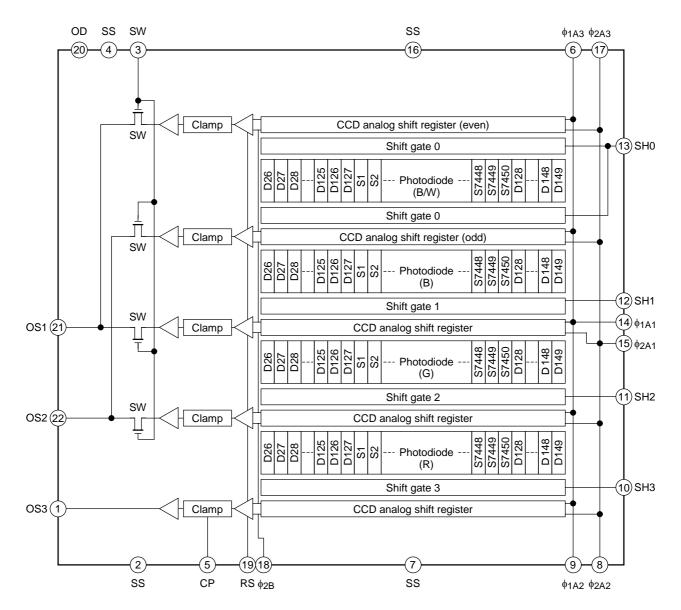
OS3 OS₂ SS OS1 SW OD RS SS СР Black&White **ф**2В Green Blue Red ф2A3 ф1Α3 SS SS 16 φ2A1 φ2A2 φ1A1 φ1A2 SH3 SH0 7450 7450 7450 SH2 SH1

Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Clock pulse voltage	$V_{\phi A}$		V
Last stage clock pulse voltage	$V_{\phi B}$		V
Shift pulse voltage	V _{SH}	-0.3~8.0	V
Reset pulse voltage	V _{RS}	-0.5~0.0	V
Clamp pulse voltage	V _{CP}		V
Switch pulse voltage	V _{SW}		V
Power supply voltage	V _{OD}	-0.3~15	V
Operating temperature	T _{opr}	0~60	°C
Storage temperature	T _{stg}	-25~85	°C

Note 1: All voltages are with respect to SS terminals (ground).

Circuit Diagram



Pin Names

OS3	Output signal 2 (rad)	000	Output signal 2 (groop DAM (add))
083	Output signal 3 (red)	OS2	Output signal 2 (green, B/W (odd))
SS	Ground	OS1	Output signal 1 (blue, B/W (even))
SW	Mode switch input (color or B/W)	OD	Power supply
SS	Ground	RS	Reset gate
СР	Clamp gate	Ф2В	Last stage transfer clock
ф1А3	Transfer clock 3 (phase 1)	Ф 2А3	Transfer clock 3 (phase 2)
SS	Ground	SS	Ground
ф2A2	Transfer clock 2 (phase 2)	Ф2 А1	Transfer clock 1 (phase 2)
ф1A2	Transfer clock 2 (phase 1)	Ф1 А1	Transfer clock 1 (phase 1)
SH3	Shift gate 3	SH0	Shift gate 0
SH2	Shift gate 2	SH1	Shift gate 1

Optical/Electrical Characteristics

 $(\bar{Ta}=25^{\circ}\text{C},\,V_{OD}=10\,\,\text{V},\,V_{\phi}=V_{RS}=V_{SH}=V_{CP}=5\,\,\text{V}$ (pulse), $f_{\phi}=1.0\,\,\text{MHz}$, load resistance = 100 k Ω , t_{INT} (integration time) = 10 ms, light source = light source A + CM500S (t = 1.0 mm))

Characteristics		Symbol	Min	Тур.	Max	Unit	Note	
	Black and white	R _{B/W}	10.2	12.8	15.4			
Sensitivity	Red	R _R	3.8	5.5	7.2	V/(lx·s)	(Note 2)	
Sensitivity	Green	R _G	5.9	8.5	11.1	V/(IX-S)	(INOLE 2)	
	Blue	R _B	2.9	4.2	5.5			
Photo reaponed non uniformity		PRNU (1)	_	10	20	%	(Note 3)	
Photo response non uniformity		PRNU (3)	_	3	12	mV	(Note 4)	
Saturation output voltage		V _{SAT}	1.0	1.5	_	V	(Note 5)	
Saturation exposure	Black and white	SE (B/W)	0.06	0.12	_	lx·s	(Note 6)	
	Color	SE (color)	0.09	0.18	_	ix.2	(Note 6)	
Dark signal voltage		V _{DRK}	_	2	5	mV	(Note 7)	
Dark signal non uniformity		DSNU	_	8	12	mV	(Note 8)	
DC power dissipation		P _D	_	400	600	mW		
Total transfer efficiency		TTE	92	97	_	%	_	
Output impedance		Z _O	_	0.2	0.5	kΩ		
DC signal output voltage	Black and white	Vos (B/W)	4.0	5.5	7.0	V	(Note 0)	
	Color	V _{OS} (color)	3.0	4.5	6.0	V	(Note 9)	
Random noise	Black and white	N _{Dσ} (B/W)	_	0.7	_	mV	(Note 10)	
Random noise	Color	N _{Dσ} (color)	_	1.4	_	IIIV	(Note 10)	

Note 2: Sensitivity is defined for each color of signal outputs average when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature.

Note 3: PRNU (1) is defined for each color on a single chip by the expressions below when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature, and the incident light is 50% of SH (typ.).

PRNU (1) =
$$\frac{\Delta X}{\overline{X}} \times 100$$
 (%)

 \overline{X} : Average of total signal outputs

 ΔX : The maximum deviation from \overline{X} .

Note 4: PRNU (3) is defined as maximum voltage with next pixel, where measured 5% of SE (typ.).

Note 5: V_{SAT} is defined as minimum saturation output voltage of all effective pixels.

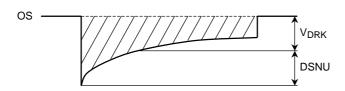
Note 6: Definition of SE:

$$\text{SE }_{\text{(B/W)}} = \frac{\text{V}_{\text{SAT}}}{\text{R}_{\text{B/W}}} \ , \ \text{SE }_{\text{(color)}} = \frac{\text{V}_{\text{SAT}}}{\text{R}_{\text{G}}}$$

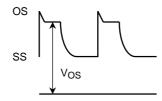
Note 7: VDRK is defined as average dark signal voltage of all effective pixels.

Note 8: DSNU is defined by the difference between average value (V_{DRK}) and the maximum value of the dark voltage.

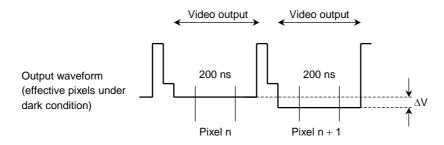
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Note 9: DC signal output voltage is defined as follows:



Note 10: Random noise is defined as the standard deviation (sigma) of the output level difference between two adjacent effective pixels under no illumination (i.e. dark condition) calculated by the following procedure.



- (1) Two adjacent pixels (pixel n and n + 1) in one reading are fixed as measurement points.
- (2) Each of the output levels at video output periods averaged over 200 nanosecond period to get Vn and Vn + 1.
- (3) Vn + 1 is subtracted from Vn to get ΔV .

$$\Delta V = V(n) - V(n+1)$$

(4) The standard deviation of ΔV is calculated after procedure (2) and (3) are repeated 30 times (30 readings).

$$\overline{\Delta V} = \frac{1}{30} \sum_{i=1}^{30} |\Delta Vi|$$

$$\sigma = \sqrt{\frac{1}{30} \sum_{i=1}^{30} (|\Delta V_i| - \overline{\Delta V})^2}$$

(5) Procedure (2), (3) and (4) are repeated 10 times to get 10 sigma values.

$$\overline{\sigma} = \frac{1}{10} \sum_{j=1}^{10} \sigma_j$$

(6) σ value calculated using the above procedure is observed $\sqrt{2}$ times larger than that measured relative to the ground level. So we specify the random noise as follows.

$$N_{D\sigma} = \frac{1}{\sqrt{2}} \overline{\sigma}$$

Operating Condition ($Ta = 25^{\circ}C$)

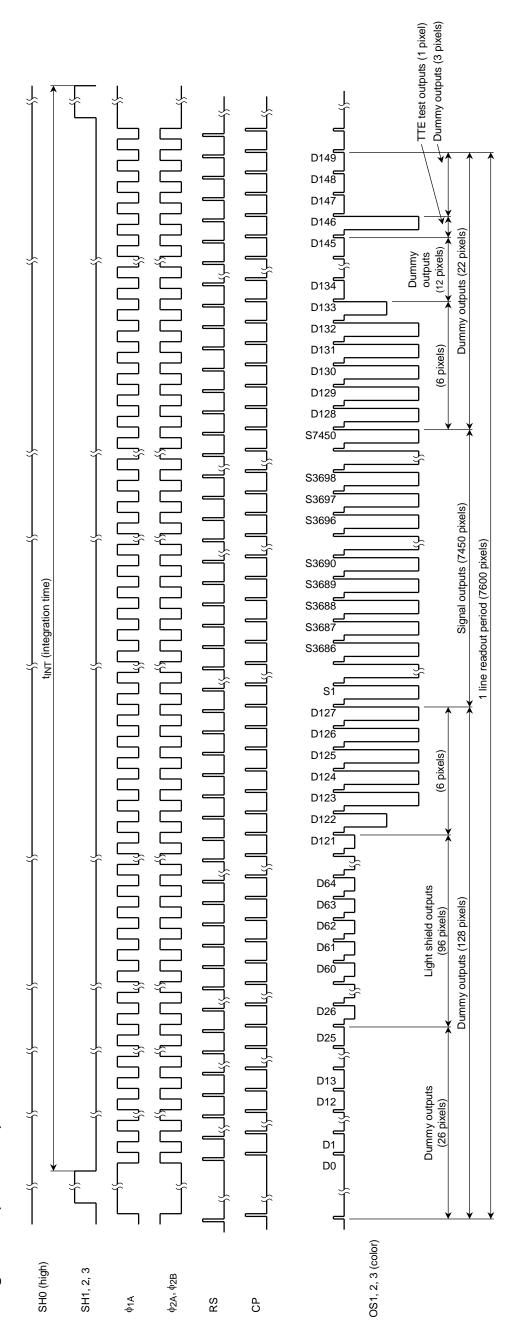
Characteristi	cs	Symbol	Min	Тур.	Max	Unit	
Clock pulse voltage	High level	$V_{\phi 1A}$	4.75	5.0	5.5	V	
Clock pulse voltage	Low level	$V_{\phi 2A}$	0	_	0.25	V	
Last stage clock pulse	High level	\/ -	4.75	5.0	5.5	V	
voltage	Low level	$V_{\phi 2B}$	0	_	0.25		
Chift pulse velters	High level	V	4.75	5.0	5.5	V	
Shift pulse voltage	Low level	V _{SH}	0	_	0.25	V	
Deact mules voltage	High level	\/	V	4.75	5.0	5.5	V
Reset pulse voltage	Low level	V_{RS}	0	_	0.25	V	
Clamp pulse valtage	High level	V	4.75	5.0	5.5	V	
Clamp pulse voltage	Low level	V _{CP}	0	_	0.25	\ \ \	
Cuitab pulsa valtaga	High level	\/	4.75	5.0	5.5	V	
Switch pulse voltage	Low level	V_{SW}	0	_	0.25	V	
Power supply voltage		V _{OD}	9.5	10.0	11.0	V	

Clock Characteristics (Ta = 25°C)

Characteristics	Symbol	Min	Тур.	Max	Unit	
Clock pulse frequency	f _{\phi} (B/W)	_	1.0	25	MHz	
Clock pulse frequency	f _φ (color)	_	1.0	20		
Reset pulse frequency	f _{RS}	_	1.0	25	MHz	
Clamp pulse frequency	f _{CP}	_	1.0	25	MHz	
Clock capacitance (Note 11)	C _{ϕ1A}	_	260	_	pF	
(Note 11)	C _{ϕ2A}	_	220	_		
Last stage clock capacitance	$C_{\phi B}$	_	20	_	pF	
Shift gate capacitance	C _{SH} (SH0, SH3)	—	20	_	pF	
Shirt gate capacitance	C _{SH} (SH1, SH2)	_	10	_	ρι	
Reset gate capacitance	C _{RS}	_	20	_	pF	
Clamp gate capacitance	C _{CP}	_	15	_	pF	
Switch gate capacitance	C _{SW}	_	10	_	pF	

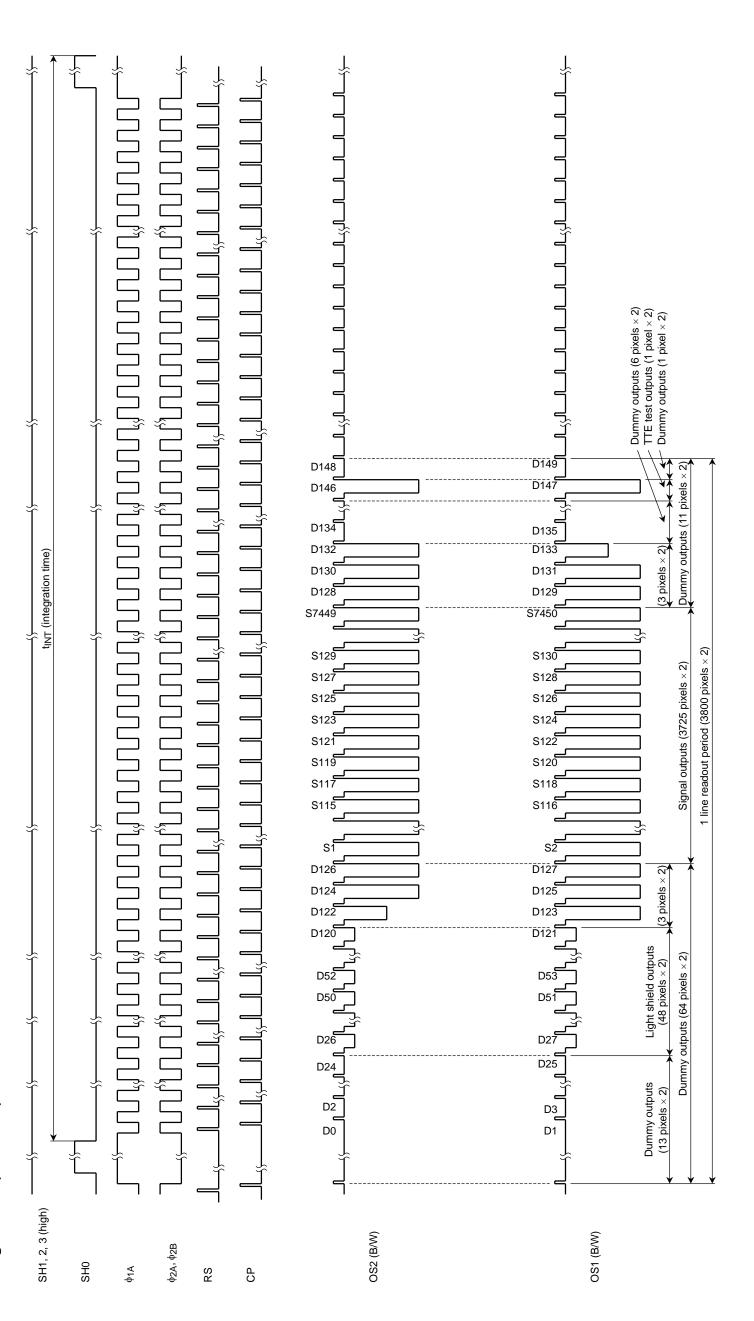
Note 11: $V_{OD} = 10 \text{ V}$

Timing Chart 1 (color mode)



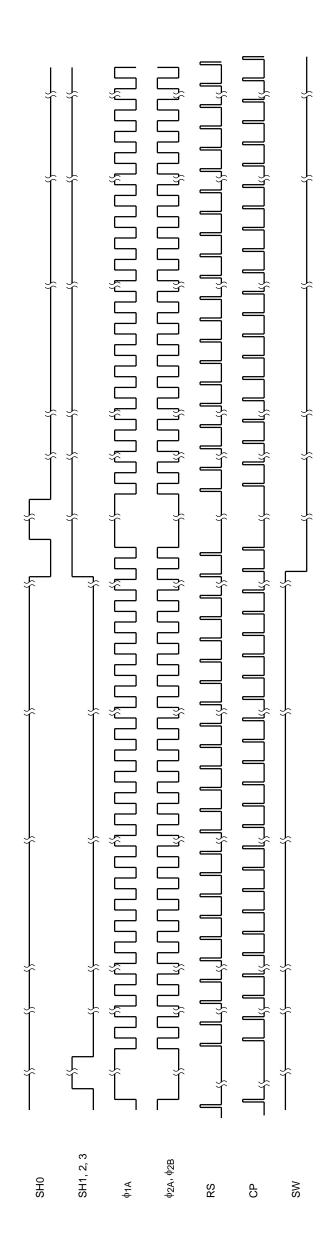
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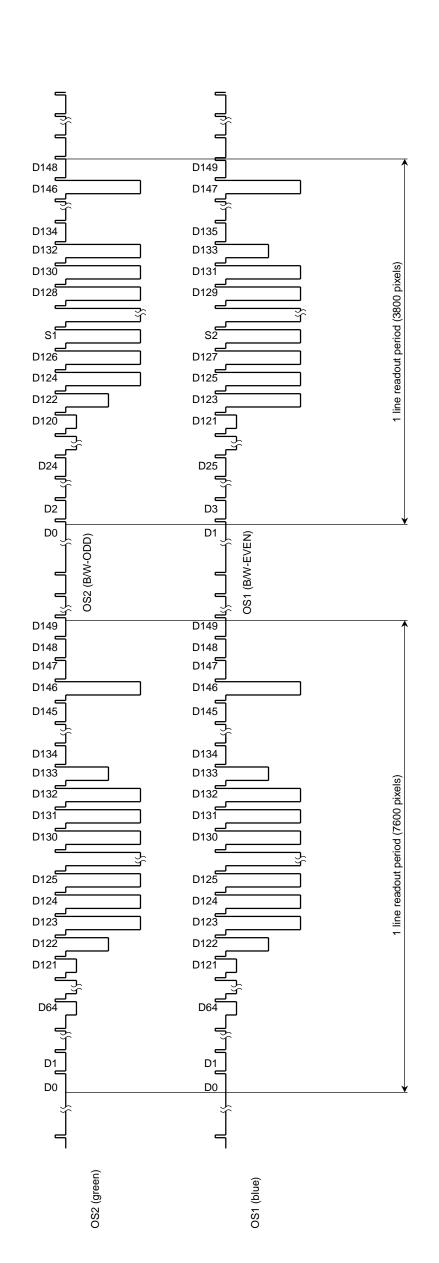
Timing Chart 2 (B/W mode)



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Timing Chart 3 (color → B/W mode)

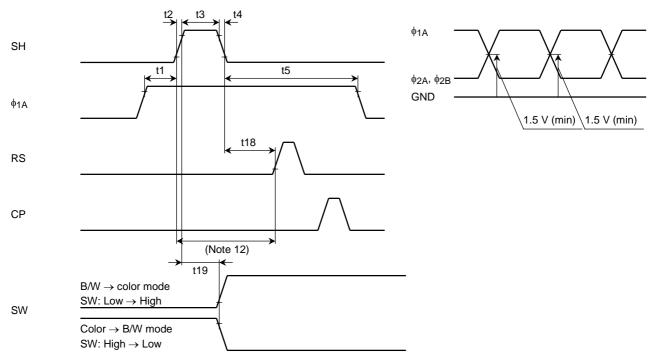




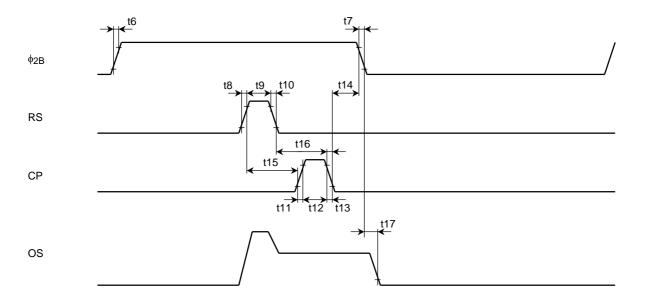
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Timing Requirements

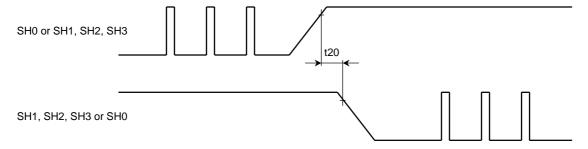


Note 12: Hold the RS and CP pins at low during this period.



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SH Input



Prohibited Combination of SH Inputs

SH1, SH2, SH3: "L" SH0: "L"

Characteristics	Symbol	Min	Typ.	Max	Unit	
Pulse timing of SH and ₀₁A	t1	120	1000	_	ns	
Fulse tilling of Sri and ψ1Α	t5	1000	1200	_	113	
SH pulse rise time, fall time	t2, t4	0	50	_	ns	
SH pulse width	t3	3000	5000	_	ns	
φ1, φ2 Pulse rise time, fall time	t6, t7	0	50	_	ns	
RS pulse rise time, fall time	t8, t10	0	20	_	ns	
RS pulse width	t9	10	100	_	ns	
CP pulse rise time, fall time	t11, t13	0	20	_	ns	
CP pulse width	t12	10	200	_	ns	
Pulse timing of φ _{2B} and CP	t14	0	40	_	ns	
Pulse timing of RS and CP	t15	0	0	_	ns	
Fuse tilling of K3 and GF	t16	10	100	_	115	
Video data delay time B/W	t17	_	10	_	no	
(Note 14) Color		_	15	_	ns	
Pulse timing of SH and RS	t18	1000	_		ns	
Pulse timing of SH and SW	t19	100	500	t3 – 100	ns	
Mode switching (color \leftrightarrow B/W) timing of SH pulse	t20	3000	5000	_	ns	

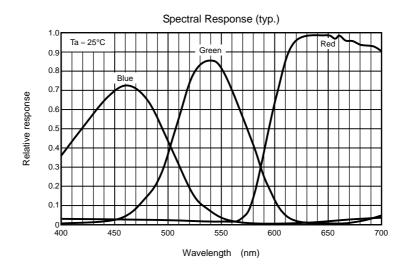
Note 12: Measured with $f_{RS} = 1$ MHz.

Note 13: Load resistance is 100 k Ω .

Mode Switch Input

Output Type	SW Input Pulse
Color	High
B/W	Low

Typical Spectral Response



Cautions

1. Electrostatic Breakdown

The dust and stain on the glass window of the package degrade optical performance of CCD sensor. Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N2. Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

- a. Prevent the generation of static electricity due to friction by making the work with bare hands or by putting on cotton gloves and non-charging working clothes.
- Discharge the static electricity by providing earth plate or earth wire on the floor, door or stand of the work room.
- c. Ground the tools such as soldering iron, radio cutting pliers of or pincer.

It is not necessarily required to execute all precaution items for static electricity. It is all right to mitigate the precautions by confirming that the trouble rate within the prescribed range.

2. Window Glass

The dust and stain on the glass window of the package degrade optical performance of CCD sensor. Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N2. Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

3. Incident Light

CCD sensor is sensitive to infrared light. Note that infrared light component degrades resolution and PRNU of CCD sensor.

4. Mounting on a PCB

This package is sensitive to mechanical stress.

Toshiba recommends using IC inserters for mounting, instead of using lead forming equipment.

5. Soldering

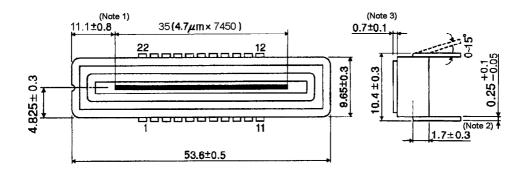
Soldering by the solder flow method cannot be guaranteed because this method may have deleterious effects on prevention of window glass soiling and heat resistance.

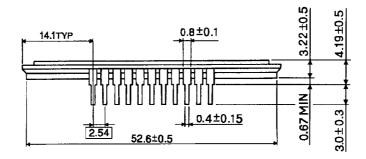
Using a soldering iron, complete soldering within ten seconds for lead temperatures of up to 260°C, or within three seconds for lead temperatures of up to 350°C.

Package Dimensions

WDIP22-G-400-2.54D

Unit: mm





Note 1: Distance between the edge of the package and the first pixel (S1)

Note 2: Distance between the of chip and bottom of the package.

Note 3: Glass thickness (n = 1.5)

Weight: 5.2 g (typ.)

RESTRICTIONS ON PRODUCT USE

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